

MAC3010, MAC3020, MAC3030, MAC3040 SERIES

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

• Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

• Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Dating	Sumbol			Current	Ratings			11
Rating	Symbol	-4	-8	-15	-25	-40	-401	Unit
RMS on-state current (full sine wave, 50 to 60Hz)	I _{T(RMS)}	4.0	8.0	15	25	40	40	Amps
Peak non-repetitive surge current								• • • • •
(1 cycle, 60 Hz, T _c = 110°C)	I _{TSM}	30	80	150	250	300	300	Amps
Circuit fusing considerations	l ² t							A ² s
(T _J = -40 to +110°C, t = 8.3ms)	ιτ	3.6	26	90	260	370	370	AS
Peak gate voltage (t ≤ 2.0µs)	V _{GM}	±5	±10	±10	±10	±10	±10	Volts
Peak gate power (t $\leq 2.0 \mu s$)	P _{GM}	10	20	20	20	20	20	Watt
Peak gate current (t≤2.0μs)	I _{GM}	11	12	12	12	12	12	Amp
Average gate power	D			0	- -	r		
(T _c = 80°C, t = 8.3ms)	P _{G(AV)}			0	.5			Watt
Operating junction temperature range	TJ	-40 to	o +100	-40 to	o +125	-40 to	o +100	°C
Storage temperature range	T _{stg}			-40 to	o +150			°C
Mounting torque	-	6.0	8.0	8.0	8.0	30	30	In. lb
Peak repetitive forward voltage								
MAC3010/MAC3030	V _{DRM}	250	250	250	250	250	250	Volts
MAC3020/MAC3040		400	400	400	400	400	400	

THERMAL CHARACTERISTICS

Characteristic	Symbol		Cu	rrent Ratii	ngs			Unit
Characteristic	Symbol	-4	-8	-15	-25	-40	-401	Unit
Thermal resistance, junction to case	R _{ejc}	3.5	2.2	2.0	1.2	0.9	0.9	°C/W
Thermal resistance, junction to ambient	R _{eja}	75	60	60	60	1.0	1.0	°C/W

ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ and either polarity of MT2 to MT1 voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
-4 CURRENT RATING	·				
Peak blocking current ⁽²⁾	lanu				mA
(Rated $V_{DRM} @ T_J = 110^{\circ}C$)	I _{DRM}	-	-	2.0	
Peak on-state voltage (either direction)	V _{TM}				Volts
$(I_{TM} = 6A \text{ peak, pulse width} \le 2 \text{ ms, duty cycle} \le 2\%)$	- 101	-	-	2.0	
Gate trigger current (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$	I _{GT}				mA
MT2(+),G(+); MT2(-),G(-)		-	-	30	



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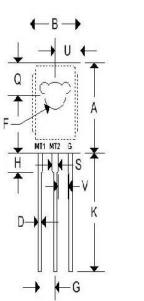
SILICON BIDIRECTIONAL THYRISTORS

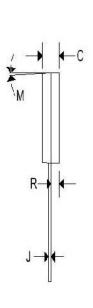
Gate trigger voltage (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$					
MT2(+),G(+); MT2(-),G(-)	V _{GT}	-	-	2.0	Volts
$(R_L = 10k\Omega, T_J = 110^{\circ}C)$					
MT2(+),G(+); MT2(-),G(-)		0.2	-	-	
Holding current					
(V_D = 12V, I_{TM} = 200mA, gate open)	IH	-	-	40	mA
Gate controlled turn on time	tgt				μs
(I _{TM} = 6A peak, I _G = 100mA)		-	1.5	-	
Critical rate of rise of commutation voltage	dv/dt(c)				V/µs
(I_{TM} = 6A peak, commutating di/dt = 3.1A/ms, gate unenergized, T _c = 85°C)		-	5.0	-	
Critical rate of rise of off-state voltage	dv/dt				V/µs
(exponential waveform, $T_c = 110^{\circ}C$)		-	20	-	

Note 2: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.

MECHANICAL CHARACTERISTICS

Case	TO-126 (MAC3010-4)
Marking	Alpha-numeric
Pin out	See below



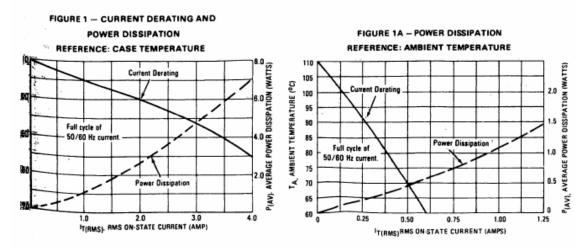


		TO	-126	
	Inc	hes	Millin	neters
	Min	Max	Min	Max
A	0.425	0.435	10.80	11.050
В	0.295	0.305	7.490	7.750
С	0.095	0.105	2.410	2.670
D	0.020	0.026	0.510	0.660
F	0.115	0.125	2.920	3.180
G	0.091	0.097	2.310	2.460
Н	0.050	0.095	1.270	2.410
J	0.015	0.025	0.380	0.640
Κ	0.595	0.655	15.110	16.640
М	3°	ТҮР	3° .	TYΡ
Q	0.148	0.158	3.760	4.010
R	0.045	0.055	1.140	1.400
S	0.025	0.035	0.640	0.890
U	0.145	0.155	3.680	3.940
۷	0.040	120	1.020	8



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SILICON BIDIRECTIONAL THYRISTORS



ELECTRICAL CHARACTERISTICS (T_c = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
-8, -15, -25 CURRENT RATING	L		I.		
Peak blocking current (2)					
(@ T _J = 125°C)	I _{DRM}	-	-	2.0	mA
Peak on-state voltage					
$(I_{TM} = \sqrt{2} I_{T(RMS)} A \text{ peak, pulse width} \le 2 \text{ ms, duty cycle} \le 2\%)$					
MAC3030-8	V _{TM}	-	-	1.6	Volts
MAC3030-15		-	-	1.6	
MAC3030-25		-	-	1.85	
Gate trigger current (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$	I _{GT}				mA
MT2(+),G(+); MT2(-),G(-)		-	-	40	
Gate trigger voltage (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$					
MT2(+),G(+); MT2(-),G(-)	V _{GT}	-	-	2.0	Volts
$(R_L = 10k\Omega, T_J = 125^{\circ}C)$					
MT2(+),G(+); MT2(-),G(-)		0.2	-	-	
Holding current					mA
$(V_D = 12V, I_{TM} = 200mA, gate open)$	I _H	-	-	40	IIIA
Gate controlled turn on time	+				
$(I_{TM} = \sqrt{2} I_{T(RMS)} A \text{ peak}, I_G = 100 \text{mA})$	t _{gt}	-	1.5	-	μs
Critical rate of rise of commutation voltage					
($I_{TM} = \sqrt{2} I_{T(RMS)} A$ peak, commutating di/dt = 0.52 $I_{T(RMS)} A$ /ms, gate unenergized,	dv/dt(c)	-	5.0	-	V/µs
T _C = 80°C)					
Critical rate of rise of off-state voltage	dv/dt				V/µs
(exponential waveform, $T_c = 125^{\circ}C$)	uv/dt	40	-	-	v/µs

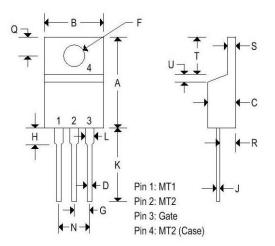


MAC3010, MAC3020, MAC3030, MAC3040 SERIES

SILICON BIDIRECTIONAL THYRISTORS

MECHANICAL CHARACTERISTICS

Case	TO-220AB (MAC3010-8, -15, -25)
Marking	Body painted, alpha-numeric
Pin out	See below



		TO-220AB						
	Inc	hes	Millim	neters				
	Min	Max	Min	Max				
Α	0.575	0.620	14.600	15.750				
В	0.380	0.405	9.650	10.290				
С	0.160	0.190	4.060	4.820				
D	0.025	0.035	0.640	0.890				
F	0.142	0.147	3.610	3.730				
G	0.095	0.105	2.410	2.670				
Н	0.110	0.155	2.790	3.930				
J	0.014	0.022	0.360	0.560				
Κ	0.500	0.562	12.700	14.270				
L	0.045	0.055	1.140	1.390				
Ν	0.190	0.210	4.830	5.330				
Q	0.100	0.120	2.540	3.040				
R	0.080	0.110	2.040	2.790				
S	0.045	0.055	1.140	1.390				
Т	0.235	0.255	5.970	6.480				
U	1	0.050		1.270				
۷	0.045	0	1.140					
Ζ	1	0.080	12	2.030				

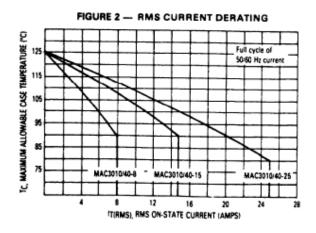
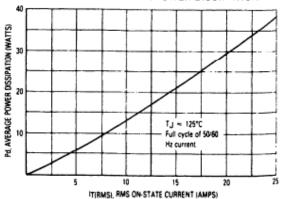


FIGURE 3 --- ON-STATE POWER DISSIPATION





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SILICON BIDIRECTIONAL THYRISTORS

Characteristic	Symbol	Min	Тур.	Max	Unit
-40, -401 CURRENT RATING					
Peak blocking current ⁽²⁾ (@ T _J = 110°C)	I _{DRM}	-	-	2.0	mA
Peak on-state voltage (either direction) (I _™ = 56A peak, pulse width ≤ 2 ms, duty cycle ≤ 2%)	V _{TM}	-	-	1.85	Volts
Gate trigger current (continuous dc) $(V_D = 12V, R_L = 100\Omega)$ MT2(+),G(+); MT2(-),G(-)	I _{GT}	-	-	40	mA
Gate trigger voltage (continuous dc) $(V_D = 12V, R_L = 100\Omega)$ MT2(+),G(+); MT2(-),G(-) $(R_L = 10k\Omega, T_J = 110^{\circ}C)$ MT2(+),G(+); MT2(-),G(-)	V _{GT}	- 0.2	-	2.0	Volt
Holding current ($V_D = 12V$, $I_{TM} = 200$ mA, gate open)	I _H	-	-	50	mA
Gate controlled turn on time $I_{TM} = 56A$ peak, $I_G = 200mA$)	t _{gt}	-	1.5	-	μs
Critical rate of rise of commutation voltage (I_{TM} = 56A peak, commutating di/dt = 22 A/ms, gate unenergized, T _c = 60°C)	dv/dt(c)	5.0	-	-	٧/μ
Critical rate of rise of off-state voltage (exponential waveform, T _c = 110°C)	dv/dt	30	-	-	V/µs

Note 2: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage



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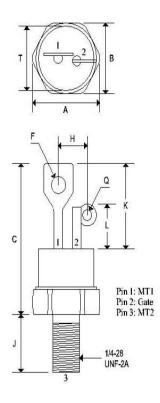
SILICON BIDIRECTIONAL THYRISTORS

MECHANICAL CHARACTERISTICS

High-reliability discrete products

and engineering services since 1977

Case TO-48 (MAC3010-40)	
Marking	Body painted, alpha-numeric
Polarity	Cathode is stud



	TO-48					
	Inc	hes	Millin	neters		
	Min	Max	Min	Max		
Α	0.604	0.614	15.340	15.600		
В	0.551	0.559	14.000	14.200		
С	1.050	1.190	2.670	30.230		
F	0.135	0.160	3,430	4.060		
Η	3.40	0.265	- 10 - 1	6.730		
J	0.420	0.455	10.670	11.560		
Κ	0.620	0.670	15.750	17.020		
L	0.300	0.350	7.620	8.890		
Q	0.055	0.085	1.400	2.160		
Т	0.501	0.505	12.730	12.830		



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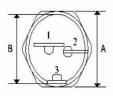
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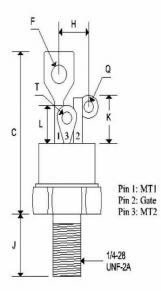
MECHANICAL CHARACTERISTICS

High-reliability discrete products

and engineering services since 1977

Case	TO-48 ISO (MAC3010-401)
Marking	Body painted, alpha-numeric
Polarity	Cathode is stud





	TO-48 ISO				
	Inches		Millimeters		
	Min	Max	Min	Max	
Α	0.551	0.559	14.000	14.200	
В	0.501	0.505	12.730	12.830	
С		1.280		32.510	
F		0.160	-	4.060	
Η	-	0.265	-	6.730	
J	0.420	0.455	10.670	11.560	
Κ	0.300	0.350	7.620	8.890	
L	0.255	0.275	6.480	6.990	
Q	0.055	0.085	1.400	2.160	
Τ	0.135	0.150	3.430	3.810	

